

General Description

The 110N08 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$. This device is suitable for PWM, load switching and general purpose applications.

Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

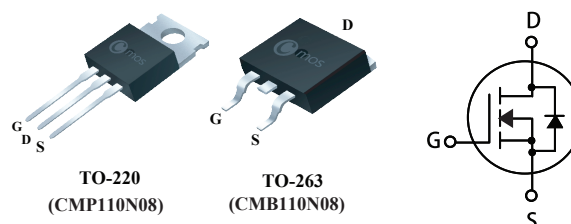
Product Summary

BVDSS	$R_{DS(ON)}$	ID
80V	6.8m Ω	110A

Applications

- Uninterruptible Power Supplies
- Battery management
- Motor control and drive

TO-220/263 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage	± 25	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current	110	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current	80	A
I_{DM}	Pulsed Drain Current	440	A
EAS	Single Pulse Avalanche Energy ¹	1322	mJ
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	250	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient(min. footprint)	---	91	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction-case	---	0.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	80	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=40A$	---	5.9	6.8	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu A$	2	---	4	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=80V$, $V_{GS}=0V$	---	---	1	μA
		$V_{DS}=80V$, $V_{GS}=0V$, $T_J=150^{\circ}\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 25V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=40A$	---	30	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1.5	---	Ω
Q_g	Total Gate Charge	$I_D=50A$	---	137	---	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=40V$	---	30	---	
Q_{gd}	Gate-Drain Charge	$V_{GS}=10V$	---	55	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=40V$ $R_{G_ext}=2.7\Omega$ $V_{GS}=10V$	---	25	---	ns
T_r	Rise Time		---	94	---	
$T_{d(off)}$	Turn-Off Delay Time		---	65	---	
T_f	Fall Time		---	96	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	7500	---	pF
C_{oss}	Output Capacitance		---	450	---	
C_{rss}	Reverse Transfer Capacitance		---	400	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	110	A
I_{SM}	Pulsed Source Current		---	---	440	A
t_{rr}	Reverse Recovery Time	$I_F=50A$	---	35	---	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100A/\mu s$	---	65	---	nC
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=40A$	---	0.86	1.4	V

Note :

1.The EAS data shows Max. rating . The test condition is $V_{DD}=50V$, $V_{GS}=10V$, $L=5\text{mH}$, $I_{AS}=23A$.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design ,functions and reliability without notice.

Typical Characteristics

